

D1

13. (Twice Amended) A polishing pad used for polishing a semiconductor wafer while supplying a polishing agent onto the polishing pad in a finish polishing process, wherein the polishing pad does not include zinc oxide (ZnO).

---

D2

20. (Three Times Amended) A polishing pad used for polishing a semiconductor wafer while supplying a polishing agent onto the polishing pad in a mirror polishing process, wherein it comprises a base layer formed of nonwoven fabric and a porous surface layer, and a content of zinc oxide (ZnO) included in the porous surface layer is 100ppm or less at the ratio of zinc weight relative to the weight of the porous surface layer.

---

D3

27. (Three Times Amended) A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 11 while supplying a polishing agent onto the polishing pad.

28. (Three Times Amended) A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 12 while supplying a polishing agent onto the polishing pad.

29. (Three Times Amended) A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 13 while supplying a polishing agent onto the polishing pad.

---

D4

30. (Twice Amended) A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 20 while supplying a polishing agent onto the polishing pad.

---

D5

31. (Three Times Amended) A method for polishing a semiconductor wafer, wherein a finish polishing is performed while supplying a polishing agent onto a polishing pad and while a concentration of zinc oxide (ZnO) is kept to 200ppm or less in a position where the semiconductor wafer is in contact with the polishing pad.

---